PIN photodiode for 0.9～1.7μm

(R&D sample)

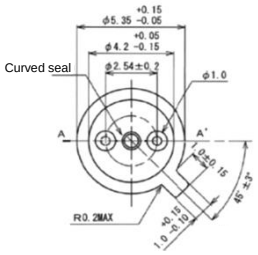
Mechanical Specifications and Materials (Unit: mm)

Package: TO-18

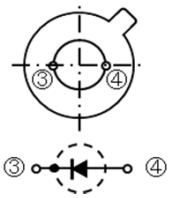
	ITEM	MATERIALS
1	STEM	SPCE, Au Plating
2	LEAD	Fe-Ni alloy, Au Plating

・Package dimensions

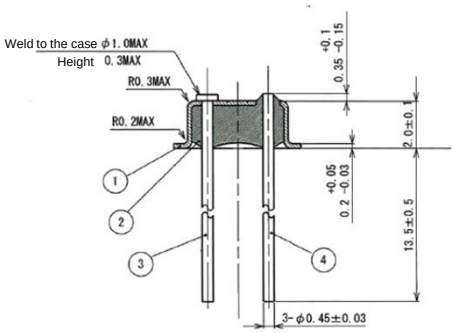
Top View



Bottom View

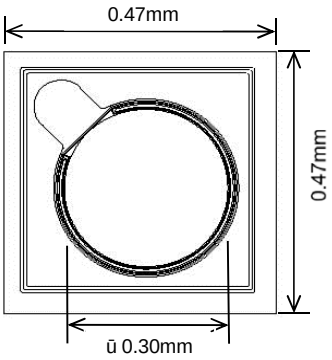


Side View (Cross Section A-A')



・Chip dimensions

Photosensitive area: ű0.30mm
Thickness 0.35mm



Typical Optical-Electrical Characteristics

T_a=25℃

Item	Symbol	Unit	
Spectral response range	ə	μm	0.9 to 1.7
Peak sensitivity wavelength	ə$_p$	μm	1.55 (Designed value)
Photosensitivity ə=1.3μm	S	A/W	0.9 (Typ.)
Photosensitivity ə=1.55μm	S	A/W	1.0 (Typ.)
Dark current (V_R=5V)	I_D	(nA)	0.20 (Typ.)
Temp. coefficient of dark current	¶TI_D	(nA)	T.B.D.

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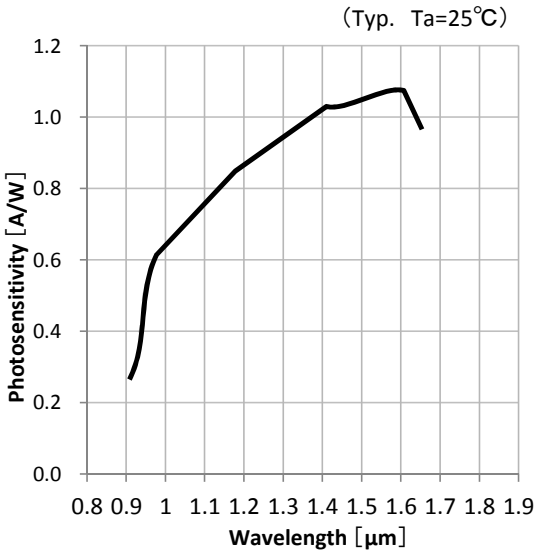
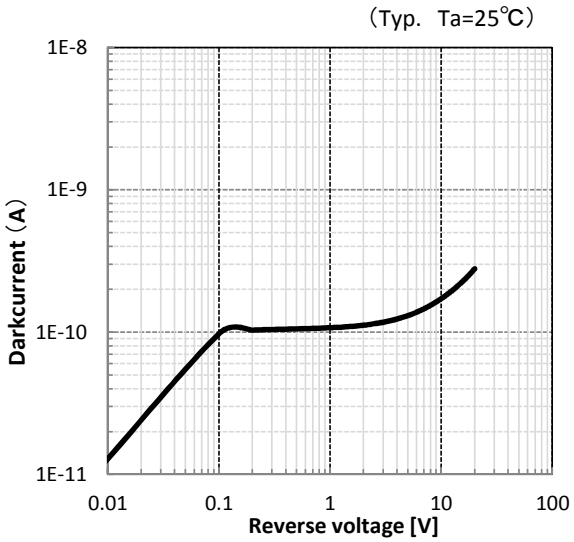
(R&D sample)

Typical properties

Spectral response



Dark current vs. reverse voltage



Terminal capacitance vs. voltage